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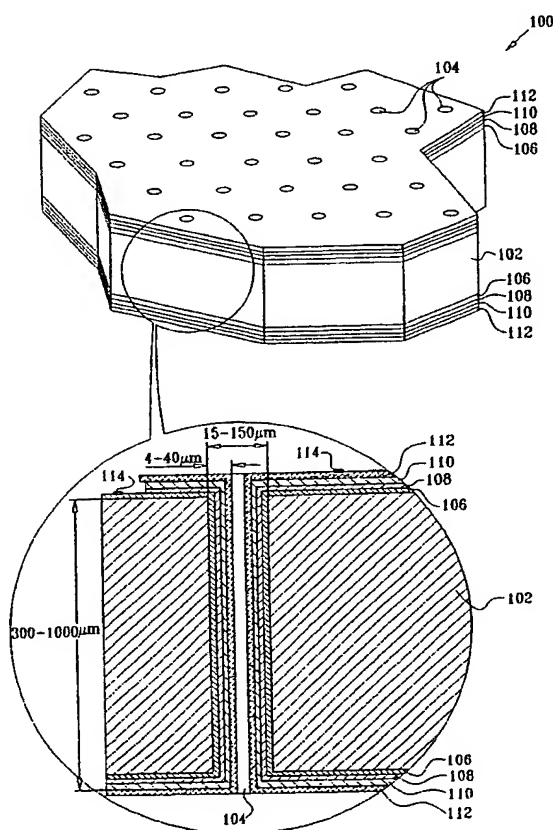
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(54) Title: **THIN-FILM CATHODE FOR 3-DIMENSIONAL MICROBATTERY AND METHOD FOR PREPARING SUCH CATHODE**



(57) Abstract: A method for producing a microbattery including providing a conductive substrate, forming a thin film cathodic layer on at least one surface of the conductive substrate, subsequently forming a thin film electrolyte layer over the cathodic layer and subsequently forming a thin film anodic layer over the electrolyte layer.

WO 2004/036668 A2



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